





DESD3Z3V3ULA

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1-Line Low Capacitance Bi-directional TVS Diode

Description

The DESD3Z3V3ULA is a 5V bi-directional TVS diode, • utilizing leading monolithic silicon technology to provide . fast re-sponse time and low ESD clamping voltage, . making this device an ideal solution for protecting voltage sensitive high-speed data lines. DESD3Z3V3ULA has a low capaci-tance with a typical value at 1pF, and complies with the IEC 61000-4-2 (ESD) with ±30kV air and ±30kV contact discharge. It is assembled into a lead-free SOD-323 package. The small size, low capacitance and high ESD surge . protection make DESD3Z3V3ULA an ideal choice to protect cell phone, wireless systems, and communication equipment.

Features

- 360W peak pulse power (8/20µs)
- Ultra low capacitance: 1pF typical
- Ultra low leakage: nA level
- Operating voltage: 3.3V
- Low clamping voltage
- Protects one power line or data line
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test Air discharge: ±30kV Contact discharge: ±30kV
 - IEC61000-4-5 (Lightning) 21A (8/20µs)
- **RoHS Compliant**

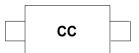
Mechanical Characteristics

- Package: SOD-323
- Lead Finish: Matte Tin
- Case Material: "Green" Molding Compound.
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Below

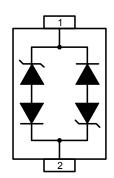
Applications

- **USB Ports**
- **Smart Phones**
- Wireless Systems
- Ethernet 10/100/1000 Base T

Marking Information



Dimensions and Pin Configuration



Circuit and Pin Schematic

Ordering Information

Part Number	Packaging	Reel Size
DESD3Z3V3ULA	3000	7 inch







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Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20µs)	Ppk	350	W
Peak Pulse Current (8/20µs)	IPP	21	А
ESD per IEC 61000-4-2 (Air)	\/ 5 00	±30	147
ESD per IEC 61000-4-2 (Contact)	VESD	±30	kV
Operating Temperature Range	TJ	-55 to +125	°C
Storage Temperature Range	Tstg	−55 to +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			3.3	V	
Punch-Through Voltage	VPT	3.5			V	IT = 2μA
Snap-Back Voltage	VBR	2.8			V	IT = 50mA
Reverse Leakage Current	I _R			0.5	μA	VRWM = 3.3V
Clamping Voltage	Vc			5	V	IPP = 1A (8 x 20μs pulse)
Clamping Voltage	Vc			16	V	IPP = 21A (8 x 20µs pulse)
Junction Capacitance	CJ		8.0	1.5	pF	VR = 0V, f = 1MHz

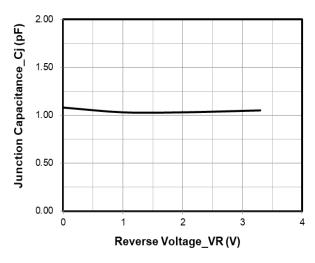




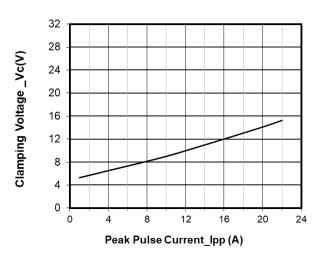
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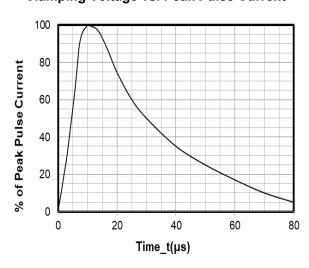
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



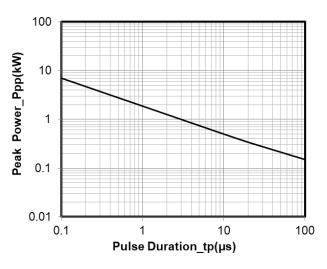
Junction Capacitance vs. Reverse Voltage



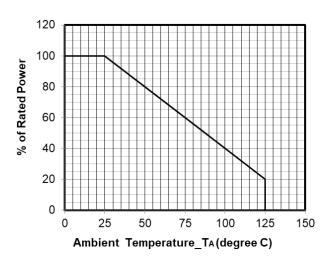
Clamping Voltage vs. Peak Pulse Current



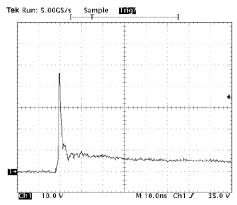
8 X 20µs Pulse Waveform



Peak Pulse Power vs. Pulse Time



Power Derating Curve



Note: Data is taken with a 10x attenuator **ESD Clamping Voltage**

8 kV Contact per IEC61000-4-2





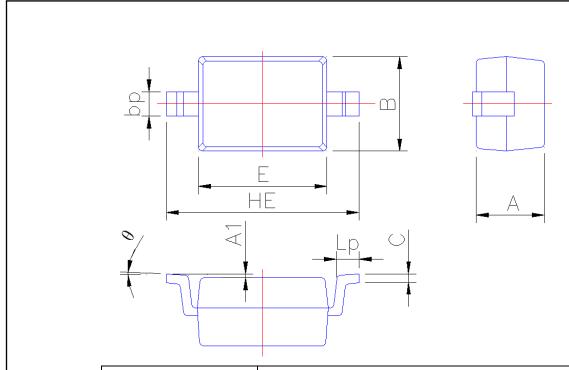
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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



Symbol	Dimension in Millimeters			
	Min	Max		
А	0.95	1.15		
A1	0.010	0.100		
В	1.20	1.40		
bp	0.25	0.40		
С	0.09	0.150		
E	1.60	1.80		
HE	2.30	2.70		
Lp	0.20	0.40		
θ	O°	5°		